## G. Device \& Process Modeling, Simulation and Reliability 분과

[TK2-G] Carrier Transport \& Ab-initio Simulation
좌장: 정창욱 교수(울산과학기술원), 장지원 교수(연세대학교)

|  | Neural Network-Assisted Acceleration of Full-Band Semi-Classical Monte Carlo Carrier Transport Simulation <br> Dong Hyeok Lee ${ }^{1}$ and Jiwon Chang ${ }^{1,2}$ <br> ${ }^{1}$ Department of Materials Science and Engineering, Yonsei University, ${ }^{2}$ Department of System Semiconductor Engineering, Yonsei University |
| :---: | :---: |
| $\begin{aligned} & \text { TK2-G-2 } \\ & \text { 11:10-11:25 } \end{aligned}$ | Cation Disorder Limited IGZO Mobility Calculation based on Density Functional Theory <br> Seung Hyo Han, Deokhwa Seo, and Mincheol Shin <br> School of Electrical Engineering, KAIST |
| $\begin{aligned} & \text { TK2-G-3 } \\ & \text { 11:25-11:40 } \end{aligned}$ | Effects of the Gate Offset on Gate-all-around Negative Capacitance Field Effect Transistors with Self-heating Effect <br> Yangjin Jung, Hyeongu Lee, and Mincheol Shin <br> Department of Electrical Engineering, KAIST |
| $\begin{aligned} & \text { TK2-G-4 } \\ & \text { 11:40-11:55 } \end{aligned}$ | Semi-Classical Monte Carlo Simulation of Electron/Hole Mobility in Monolayer $\mathrm{MX}_{2}$ ( $\mathrm{M}=\mathrm{Mo}, \mathrm{W}$; $\mathrm{X}=\mathrm{S}$, Se ) <br> Sukhyeong Youn ${ }^{1,2}$, Donghyeok Lee ${ }^{1,2}$, and Jiwon Chang ${ }^{1,2}$ <br> ${ }^{1}$ Department of System Semiconductor Engineering, Yonsei University, <br> ${ }^{2}$ Department of Materials Science \& Engineering, Yonsei University |
| $\begin{aligned} & \text { TK2-G-5 } \\ & \text { 11:55-12:10 } \end{aligned}$ | Study of Non-equilibrium Energetics in Van der Waals Ferroelectric Tunnel Junctions Using Multi-space Density Functional Theory Kaptan Rajput, Ryong Gyu Lee, Tae Hyung Kim, and Yong-Hoon Kim School of Electrical Engineering, KAIST |
| $\begin{aligned} & \text { TK2-G-6 } \\ & \text { 12:10-12:25 } \end{aligned}$ | Strain-Tuned Ferroelectric Transitions in $\mathrm{HfO}_{2}$ : A New Pathway to Ferroelectric Devices <br> \|| Young Lee ${ }^{1,2}$ and Jae Jun Yu ${ }^{1,2}$ <br> ${ }^{1}$ Center for Theoretical Physics, Seoul National University, ${ }^{2}$ Department of Physics and Astronomy, Seoul National University |


|  | 31회 한국반도치학술대회 <br> 31st Korean Conference on Semiconductors |
| :---: | :---: |
| 2024년 1월 24일(수)-26일(금)\| 경주화백컨벤션센터(HICO) |  |
| $\begin{aligned} & \text { TK2-G-7 } \\ & \text { 12:25-12:40 } \end{aligned}$ | Transport Simulation for Nanosheet FET with Extended Source and Drain Regions <br> Phil-Hun Ahn and Sung-Min Hong <br> School of Electrical Engineering and Computer Science, GIST |

